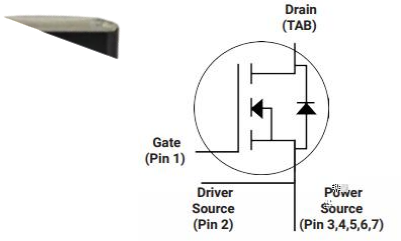
SG2M018120J1J

TriQSiC™ 1200V Silicon Carbide Power MOSFET G2

Features

-
-
-
-
-
-
-



Benefits

-
-
-
-
-

Halogen-Free

RoHS

Applications

-
-
-
-

Table 1 Key performance and package parameters

Type	V_{DS}	I_{DS}	$R_{DS(on),\ typ}$	$T_{J,max}$	Marking	Package

SG2M018120J1J

1 Maximum ratings

Table 2 Maximum rating

Symbol	Parameter	Value	Unit	Test Conditions	Note
				≤	

3 Electrical characteristics

3.1 Static characteristics

Table 4 Static characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note

3.3 Switching characteristics

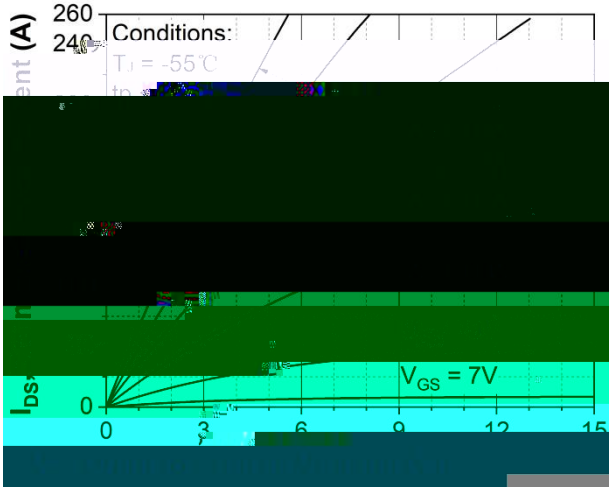
Table 6 Dynamic characteristics

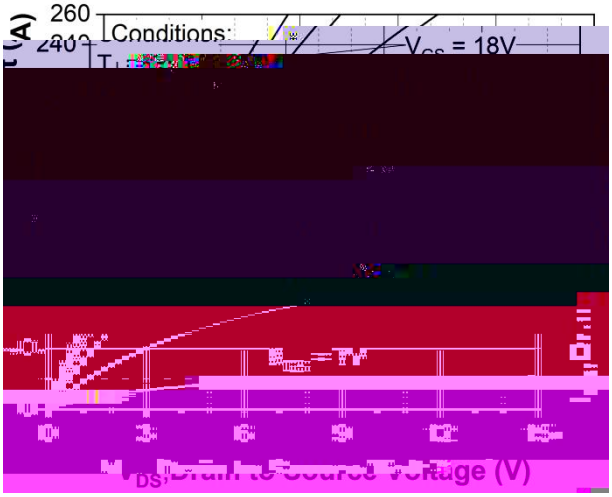
Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note

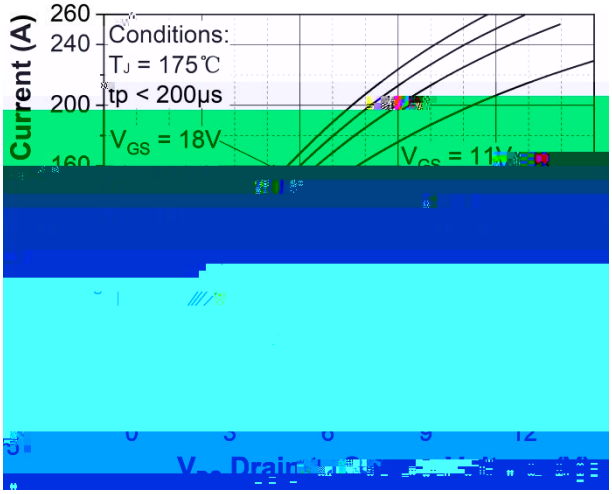
Table 7 Body diode characteristics

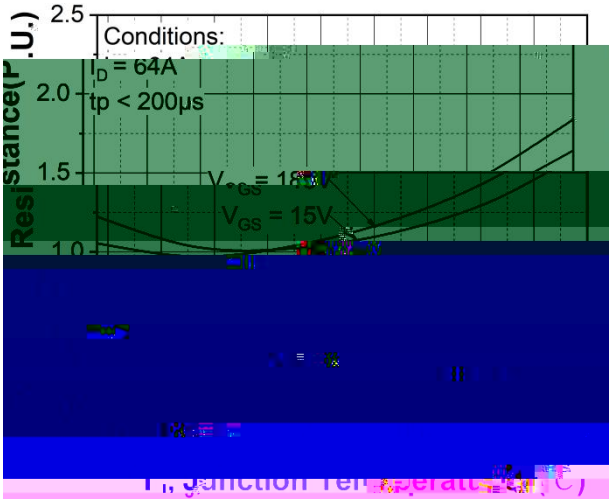
Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note

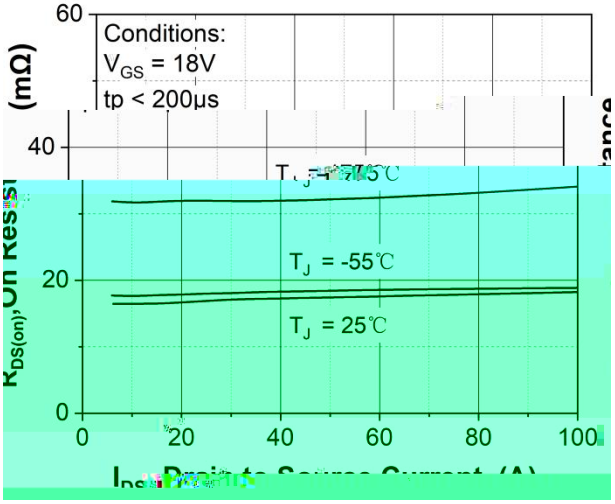
4 Electrical characteristic diagrams

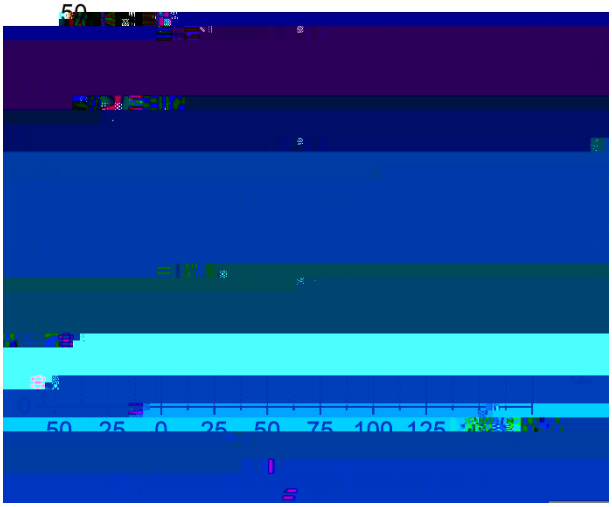




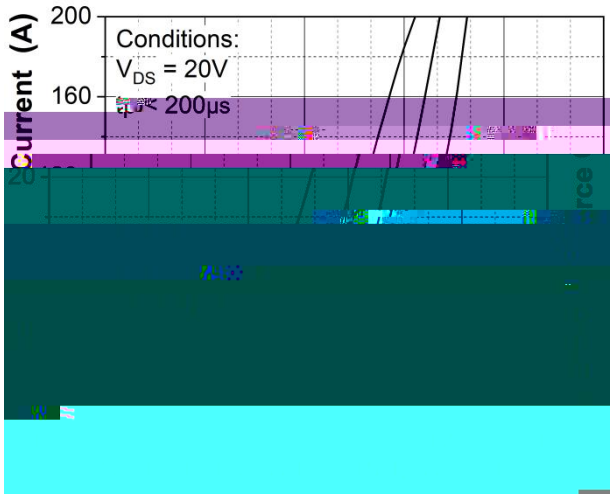


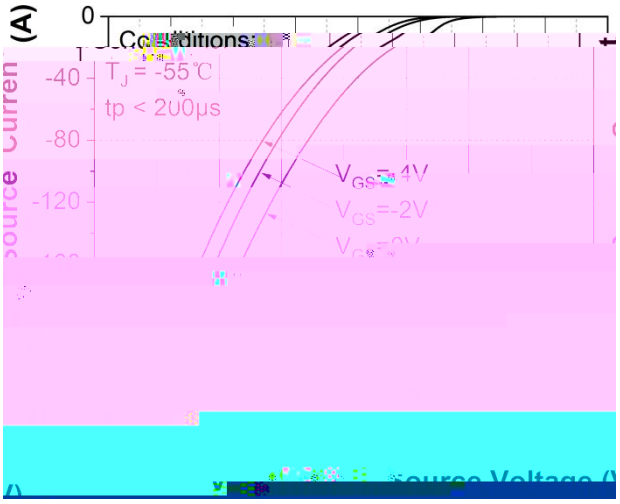


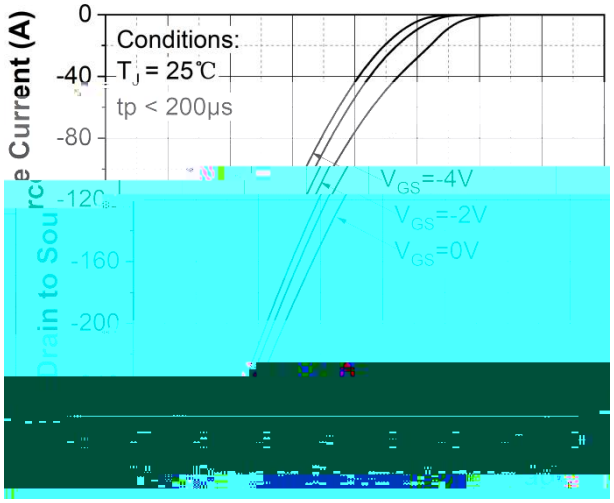


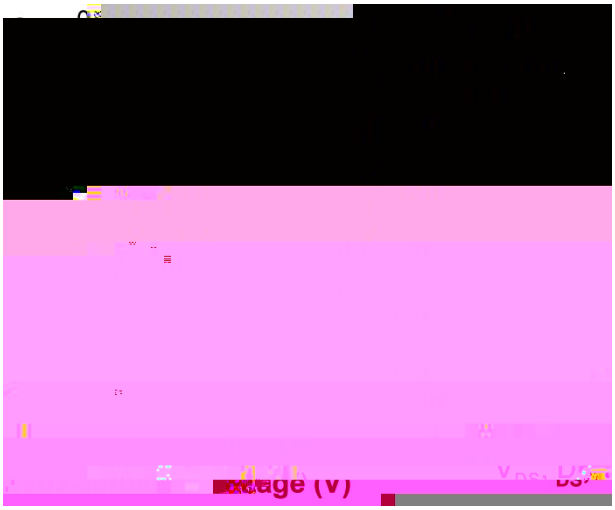


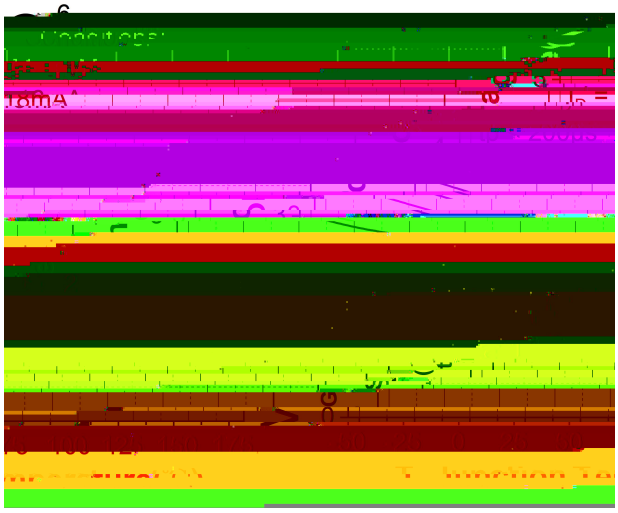
SG2M018120J1J

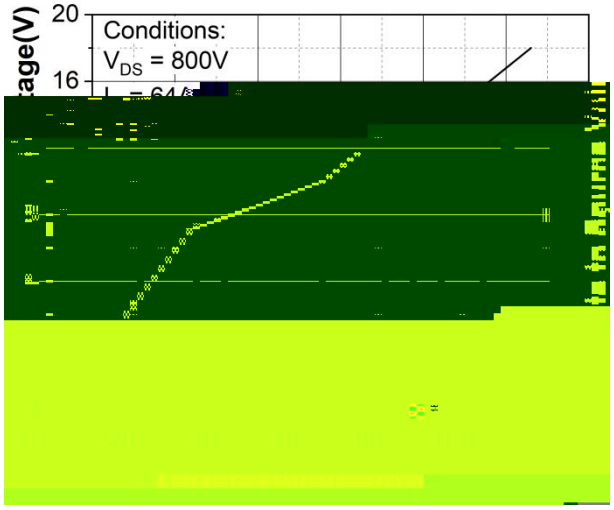




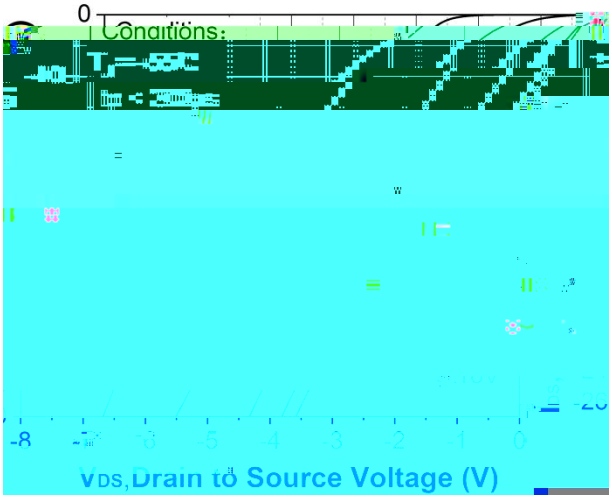


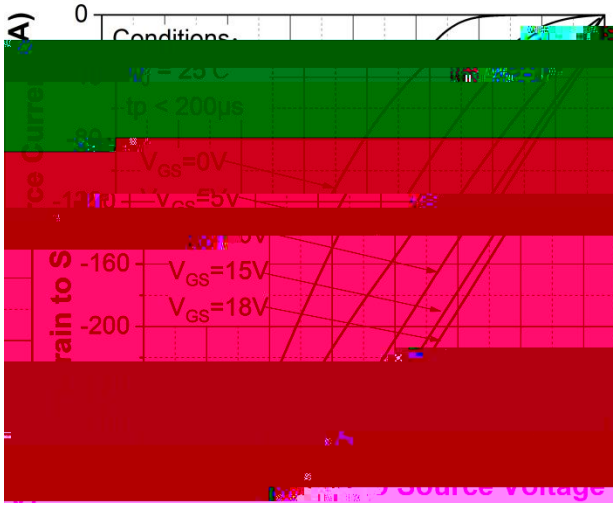


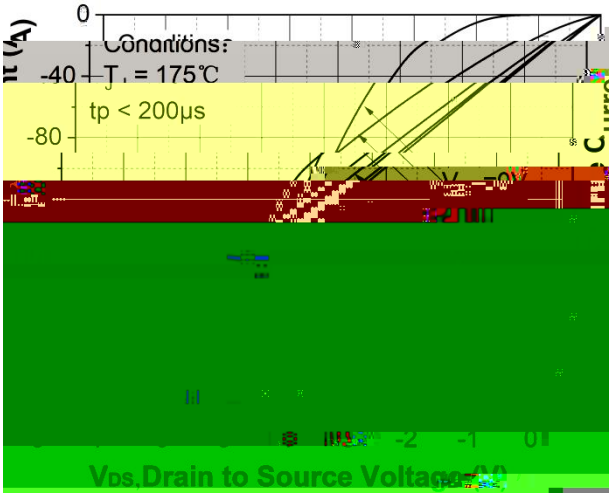


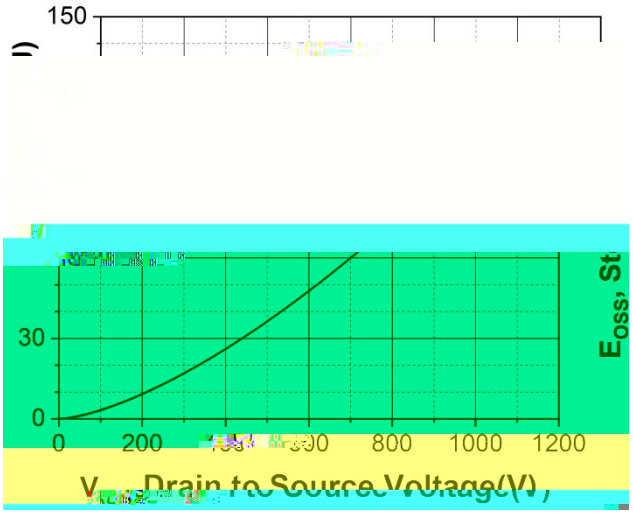


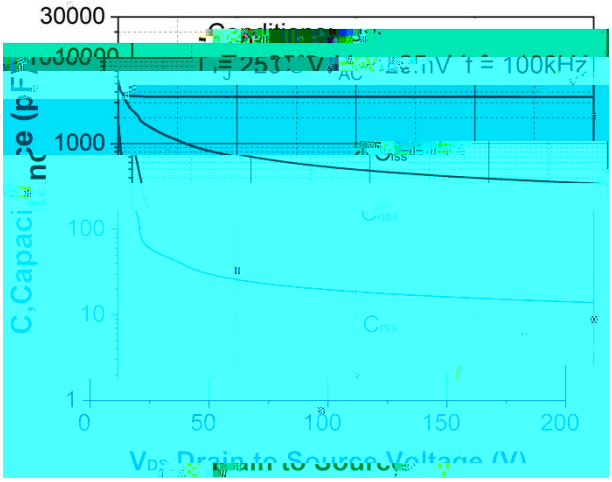
SG2M018120J1J

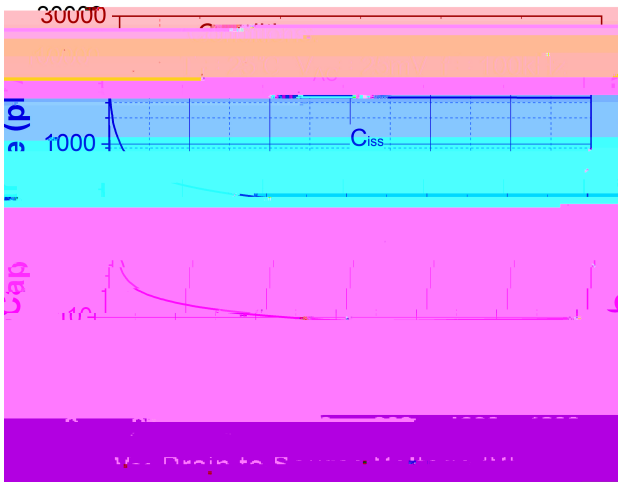




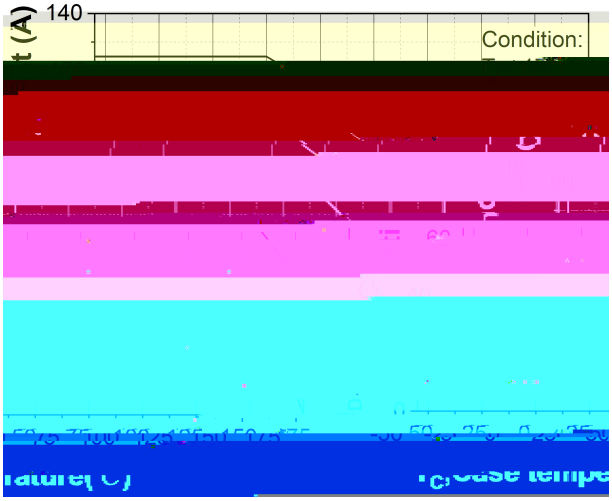


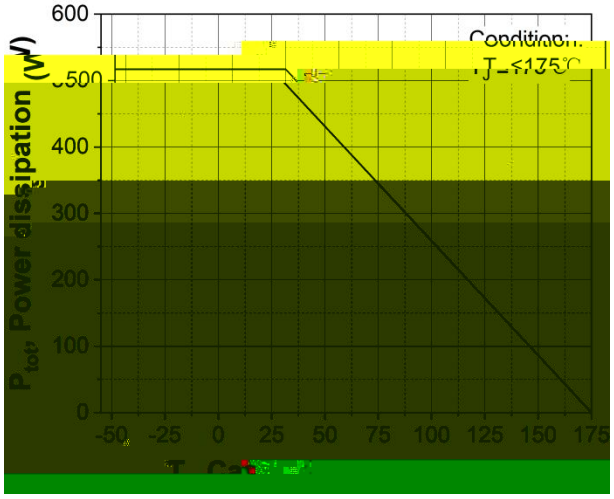


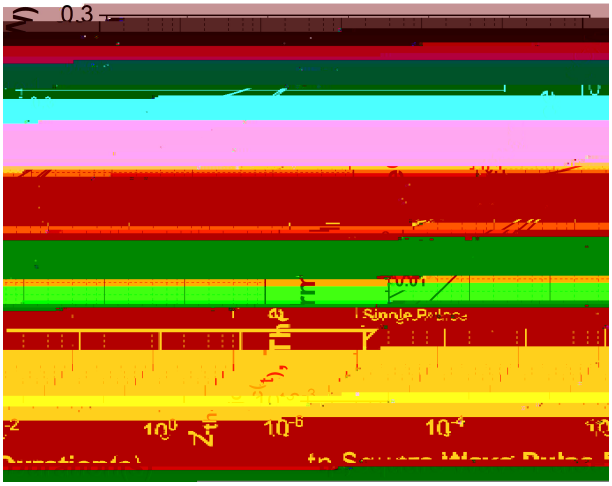


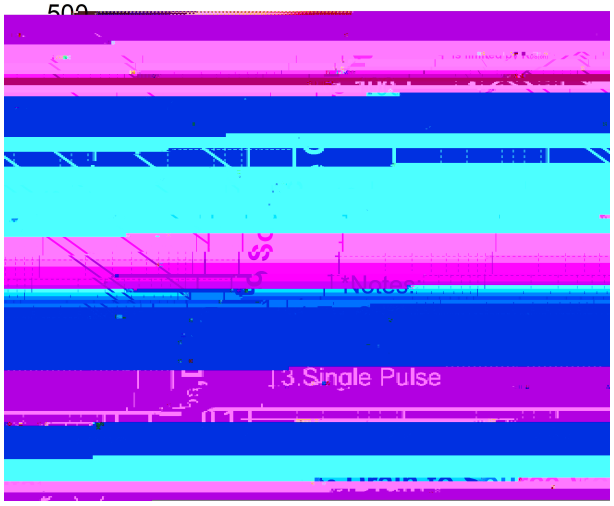


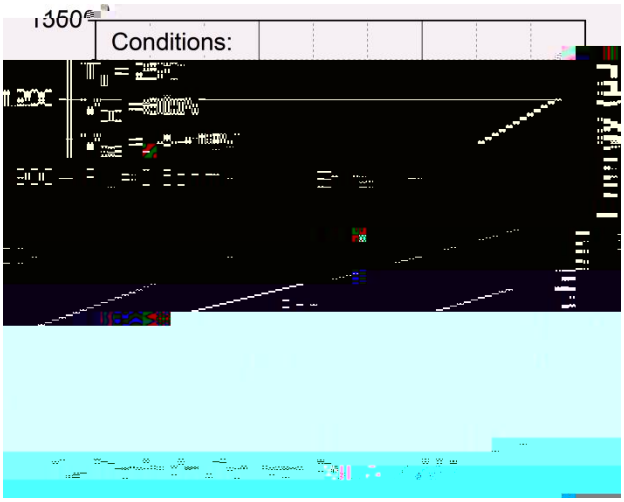
SG2M018120J1J

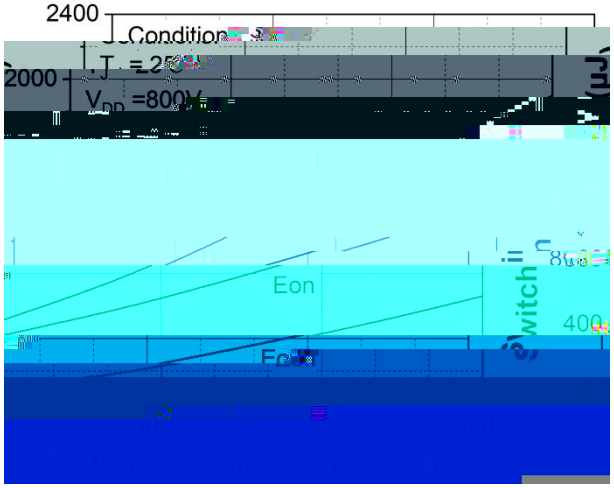




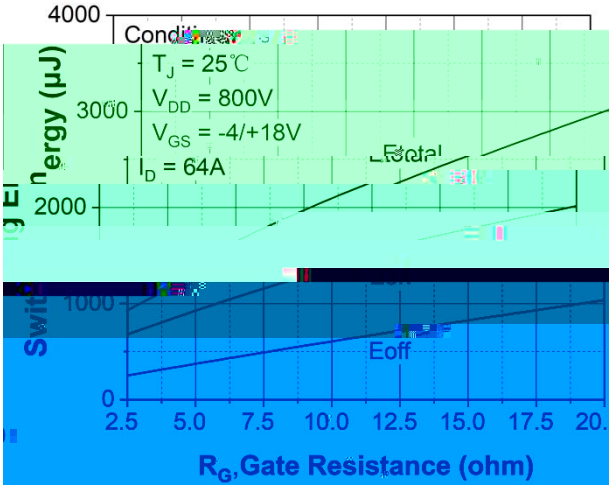


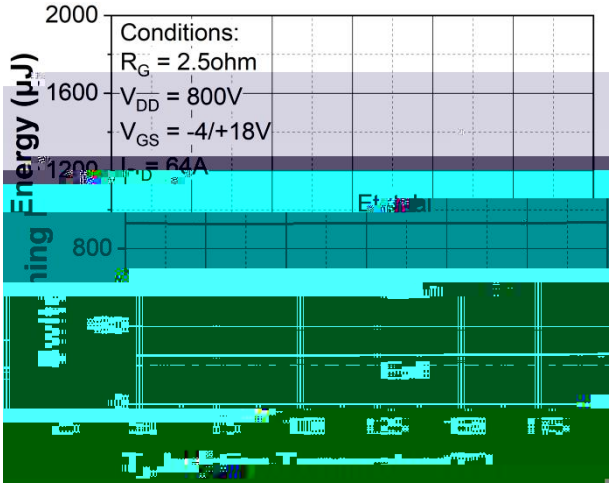


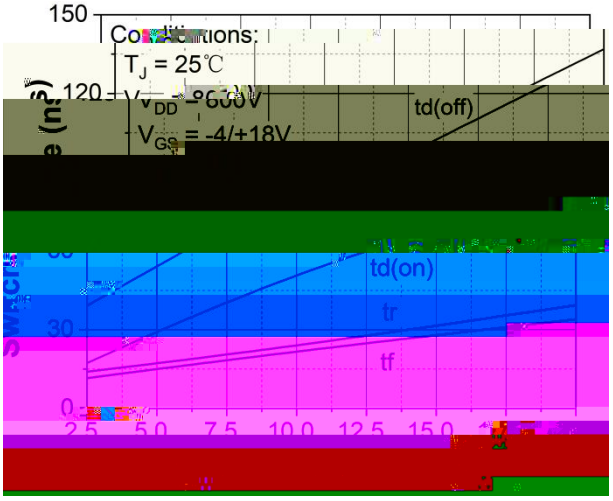




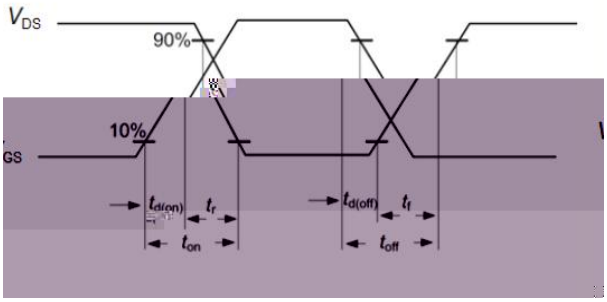
SG2M018120J1J

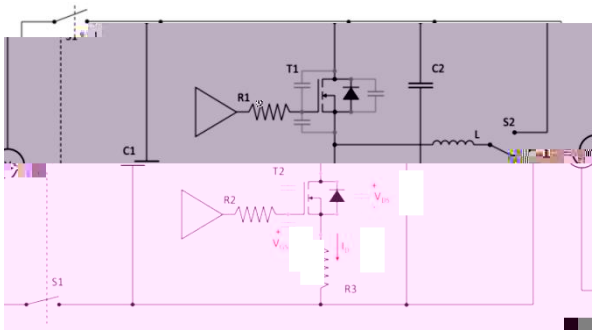


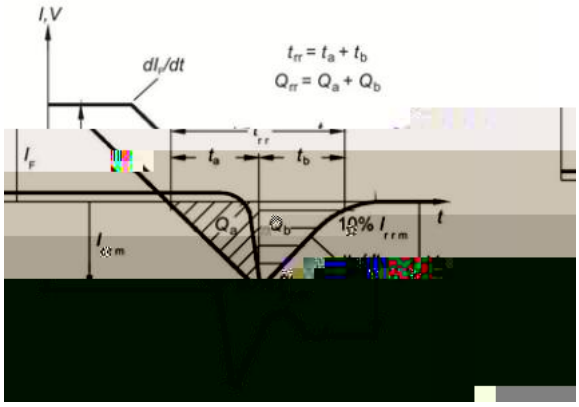




6 Test conditions







SG2M018120J1J

SG2M018120J1J